Session Title:	[TuB2] Nitrides for Electronics - II
Session Date:	July 14 (Tue.), 2026
Session Time:	10:35-12:20
Session Room:	Room B (Baekrok Hall B-2, 1F)
Session Chairs	

[TuB2-1] [Invited] 10:35-11:05

AlN-Based Heteroepitaxy and Devices by MOCVD

Xiaohang Li, King Abdullah University of Science and Technology, Saudi Arabia

[TuB2-2] 11:05-11:20

Record-High 2DEG Mobility in GaN HEMTs on an Improved AlN Buffer with a 50-nm GaN Channel

M. Hino, S. Yoshida, I. Makabe, K. Makiyama, J. Kotani, and K. Nakata, Sumitomo Electric Industries, Ltd., Japan

[TuB2-3] 11:20-11:35

Prospects and Challenges for N-Polar AlN-Based GaN Channel HEMTs

Markus Pristovsek[1], Yoann Robin[1], Itsuki Furuhashi[1], Chengzhi Zhang[2], Martin Kuball[2], Matthew D. Smith[2], Sheng Zhang[3], Xinhua Wang[3], and Xu Yang[1,3], [1] Nagoya University, Japan, [2] University of Bristol, United Kingdom, [3] Chinese Academy of Sciences, China

[TuB2-4] 11:35-11:50

Suppress the Parasitic Leakage Current of Homoepitaxial GaN HEMT Using Self-Organizing Nucleated AlN Isolation Layer

JunShuai Xue, WenBo Sun, GuanLin Wu, Cheng Zhao, ChenKai Zhang, JinCheng Zhang, and Yue Hao, Xidian University, China

[TuB2-5] 11:50-12:05

Homoepitaxial Growth of AlGaN Drift Layers on Bulk Ammonothermal GaN and AlGaN Substrates

Pawel Prystawko, Tomasz Sochacki, Robert Kucharski, Piotr Kruszewski, and Marcin Krysko, Institute of High Pressure Physics PAS, Poland

[TuB2-6] 12:05-12:20

GaN-on-GaN Regrowth Interface Optimization in MOVPE for Electronic Device Structures

F. Brunner, A. Bassal, K. Tetzner, O. Hilt, S. Breuer, and M. Weyers, Ferdinand-Braun-Institut, Germany